

SEMITOP® 3

3-phase bridge rectifier + brake chopper +3-phase bridge inverter SK 15 DGDL 126 ET

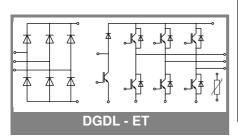
Preliminary Data

Features

- · Compact design
- · One screw mounting
- Heat transfer and isolation through direct copper bonded alumium oxide ceramic (DCB)
- Trench technology IGBT
- CAL High Density FWD
- Integrated NTC temperature sensor

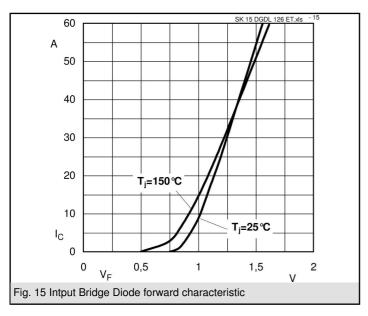
Typical Applications

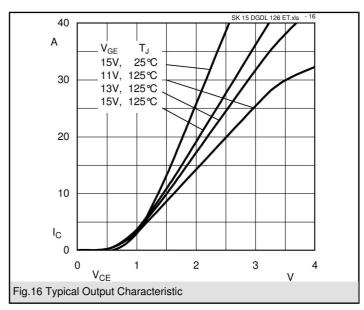
Inverter

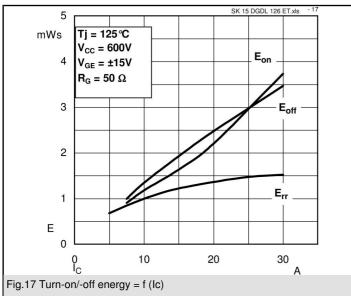


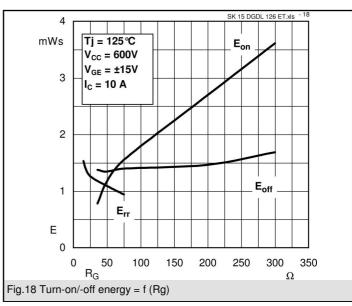
Absolute Maximum Ratings T _s = 25°C, unless otherwise specified								
Symbol	Conditions	Values	Units					
IGBT - Inverter, Chopper								
V _{CES}		1200	V					
I _C	T _s = 25 (80) °C	22 (15)	A					
I _{CRM}	$I_{CRM} = 2 \times I_{Cnom}, t_p = 1 \text{ ms}$	30	A					
V_{GES}		±20	V					
T _j		-40 +150	°C					
Diode - Inverter, Chopper								
I _F	T _s = 25 (80) °C	25 (17)	Α					
I _{FRM}	$I_{FRM} = 2xI_{Fnom}, t_p = 1 \text{ ms}$	30	Α					
$ T_j $		-40 + 150	°C					
Rectifier								
V_{RRM}		1600	V					
I _F	T _s = 80 °C	21	Α					
I _{FSM} / I _{TSM}	$t_p = 10 \text{ ms}$, sin 180 ° , $T_i = 25 \text{ °C}$	220	Α					
I ² t	t _p = 10 ms , sin 180 ° ,T _i = 25 °C	240	A²s					
$ T_j $		-40 + 150	°C					
T _{sol}	Terminals, 10s	260	°C					
T _{stg}		-40 +125	°C					
V _{isol}	AC, 1 min. / 1s	2500 / 3000	V					

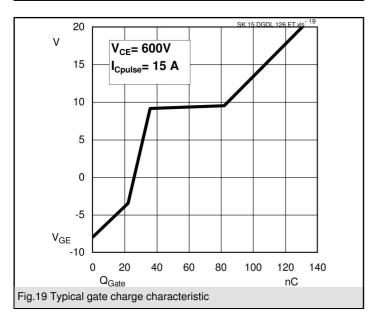
Characteristics		T _s = 25°C, unless otherwise specified							
Symbol	Conditions	min.	typ.	max.	Units				
IGBT - Inverter, Chopper									
V _{CEsat} V _{GE(th)} V _{CE(TO)} r _T C _{ies}	$I_{C} = 15 \text{ A}, T_{j} = 25 (125) ^{\circ}\text{C}$ $V_{GE} = V_{CE}, I_{C} = 0,6 \text{ mA}$ $T_{j} = 25 ^{\circ}\text{C} (125) ^{\circ}\text{C}$ $T_{j} = 25 ^{\circ}\text{C} (125) ^{\circ}\text{C}$ $V_{CE} = 25 V_{GE} = 0 \text{ V}, f = 1 \text{ MHz}$	5	1,7 (2) 5,8 1 (0,9) 45 (70) 1,2	2,1 6,5	V V V mΩ nF				
C _{oes} C _{res} R _{th(j-s)}	V_{CE} = 25 V_{GE} = 0 V, f = 1 MHz V_{CE} = 25 V_{GE} = 0 V, f = 1 MHz per IGBT		0,1 9,1	1,6	nF nF K/W				
$\begin{aligned} & t_{d(on)} \\ & t_r \\ & t_{d(off)} \\ & t_f \\ & E_{on} \\ & E_{off} \end{aligned}$	under following conditions $V_{CC} = 600 \text{ V}, V_{GE} = \pm 15 \text{ V}$ $I_{C} = 15 \text{ A}, T_{j} = 125 \text{ °C}$ $R_{Gon} = R_{Goff} = 30 \Omega$ inductive load		25 25 385 90 2 1,8		ns ns ns ns mJ				
	verter, Chopper								
$V_{F} = V_{EC}$ $V_{(TO)}$ r_{T} $R_{th(j-s)}$	$I_F = 15 \text{ A}, T_j = 25 (125) ^{\circ}\text{C}$ $T_j = 25 ^{\circ}\text{C} (125) ^{\circ}\text{C}$ $T_j = 25 ^{\circ}\text{C} (125) ^{\circ}\text{C}$ per diode		1,6 (1,6) 1 (0,8) 40 (53)	2,1	V V mΩ K/W				
I _{RRM} Q _{rr} E _{rr}	under following conditions $I_F = 15 \text{ A}, V_R = 600 \text{ V}$ $V_{GE} = 0 \text{ V}, T_j = 125 ^{\circ}\text{C}$ $di_{F/dt} = 900 \text{ A/}\mu\text{s}$		25 3 1,1		Α μC mJ				
Diode rec	Diode rectifier								
$V_{F} \\ V_{(TO)} \\ r_{T} \\ R_{th(j-s)}$	$I_F = 15 \text{ A}, T_j = 25 \text{ °C}$ $T_j = 150 \text{ °C}$ $T_j = 150 \text{ °C}$ per diode		1,1 0,9 20	2	V V mΩ K/W				
Temperatur sensor									
R _{ts}	5 %, T _r = 25 (100) °C		5000(493)		Ω				
Mechanic w	al data		30		g				
M _s	Mounting torque			2,5	Nm				

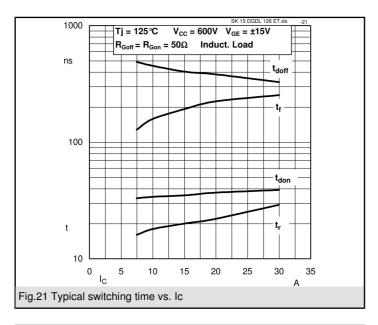


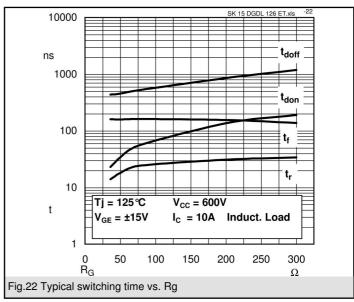


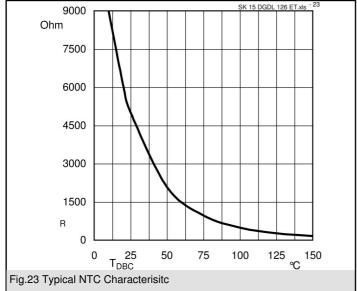


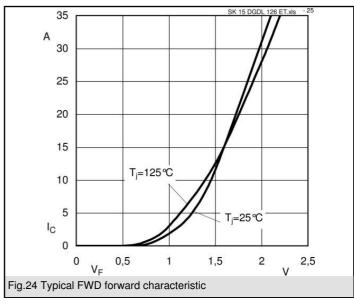


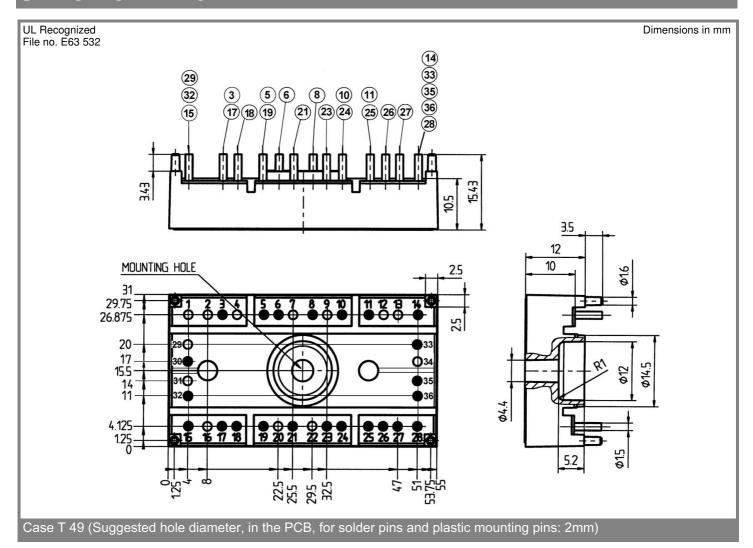


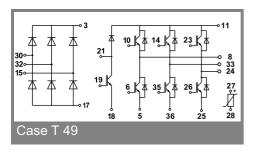












This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

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